

FDP7042L / FDB7042L

N-Channel Logic Level PowerTrench® MOSFET

General Description

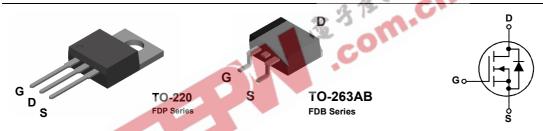
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for "low side" synchronous rectifier operation, providing an extremely low $R_{\text{DS}(\text{ON})}\,.$

Applications

- · Synchronous rectifier
- DC/DC converter

Features

- 50 A, 30 V. $R_{DS(ON)} = 9 \text{ m}\Omega$ @ $V_{GS} = 4.5 \text{ V}$ $R_{DS(ON)} = 7.5 \text{ m}\Omega$ @ $V_{GS} = 10 \text{ V}$
- Critical DC electrical parameters specified at elevated temperature
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS}(\mbox{\scriptsize ON})}$
- 175°C maximum junction temperature rating



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage	30	V	
V _{GSS}	Gate-Source Voltage	± 12	V	
I _D	Drain Current - Continuous	(Note 1)	50	Α
	– Pulsed	(Note 1)	150	
P _D	Total Power Dissipation @ T _C = 25°C	83	W	
	Derate abo	0.48	W°C	
T _J , T _{STG}	Operating and Storage Junction Tempera	-65 to +175	°C	

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.8	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

Package Marking and Ordering Information

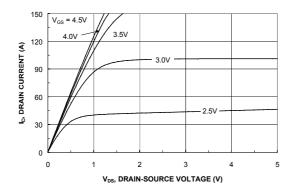
Device Marking	Device	Reel Size	Tape width	Quantity
FDB7042L	FDB7042L	13"	24mm	800 units
FDP7042L	FDP7042L	Tube	n/a	45

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics		l .	I.	U.	I.
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		24		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V			1	μΑ
I _{GSSF}	Gate-Body Leakage, Forward	V _{GS} = 12 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	V _{GS} = -12 V V _{DS} = 0 V			-100	nA
On Char	racteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	8.0	1.2	2	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		-4.1		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	V_{GS} = 4.5 V, I_{D} = 25A V_{GS} = 10 V, I_{D} = 25A V_{GS} = 4.5 V, I_{D} = 25A, T_{J} = 125°C	a	6.2 5.5 9.6	9 7.5 16	mΩ
I _{D(on)}	On–State Drain Current	$V_{GS} = 4.5 \text{ V}, \qquad V_{DS} = 10 \text{ V}$	60			Α
g FS	Forward Transconductance	$V_{DS} = 5V$, $I_{D} = 25 A$		117		S
Dynamic	Characteristics	27				
C _{iss}	Input Capacitance			2418		pF
C _{oss}	Output Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		549		pF
C _{rss}	Reverse Transfer Capacitance	f = 1.0 MHz		243		pF
Switchin	ng Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time			21	34	ns
t _r	Turn-On Rise Time	$V_{DD} = 15 \text{ V}, I_D = 1 \text{ A},$		20	32	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 4.5 V, R_{GEN} = 6 Ω		60	96	ns
t _f	Turn-Off Fall Time			30	48	ns
Q _g	Total Gate Charge			32	51	nC
Q _{gs}	Gate-Source Charge	$V_{DS} = 15 \text{ V}, I_{D} = 50 \text{ A},$ $V_{GS} = 4.5 \text{ V}$		10		nC
Q_{gd}	Gate-Drain Charge	V 65 T.O V		9		nC
Drain-S	ource Diode Characteristics a	and Maximum Ratings				
Is	Maximum Continuous Drain-Source [50	Α
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 25 A (Note 2)		0.8	1.3	V

Notes:

- 1. Maximum continuous current is limited by the package.
- 2. Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%

Typical Characteristics



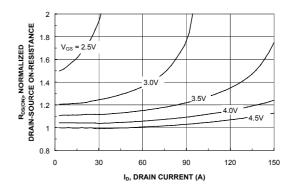
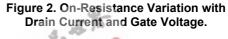
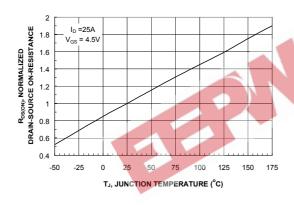


Figure 1. On-Region Characteristics.





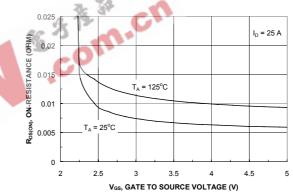
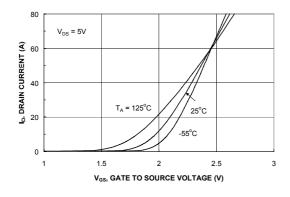


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



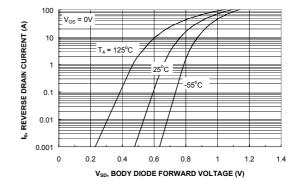
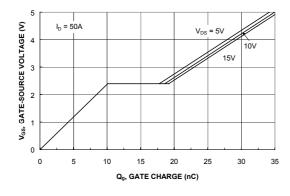


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



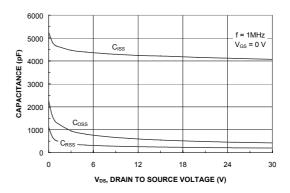
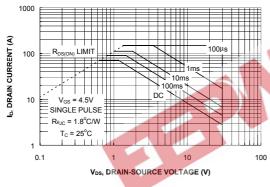


Figure 7. Gate Charge Characteristics.





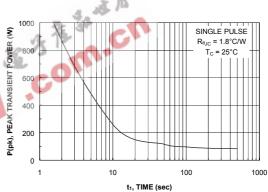


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

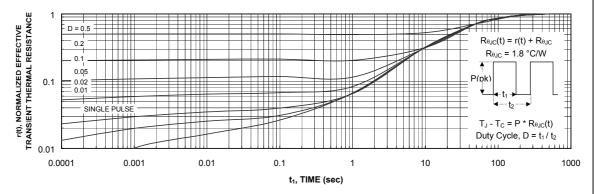
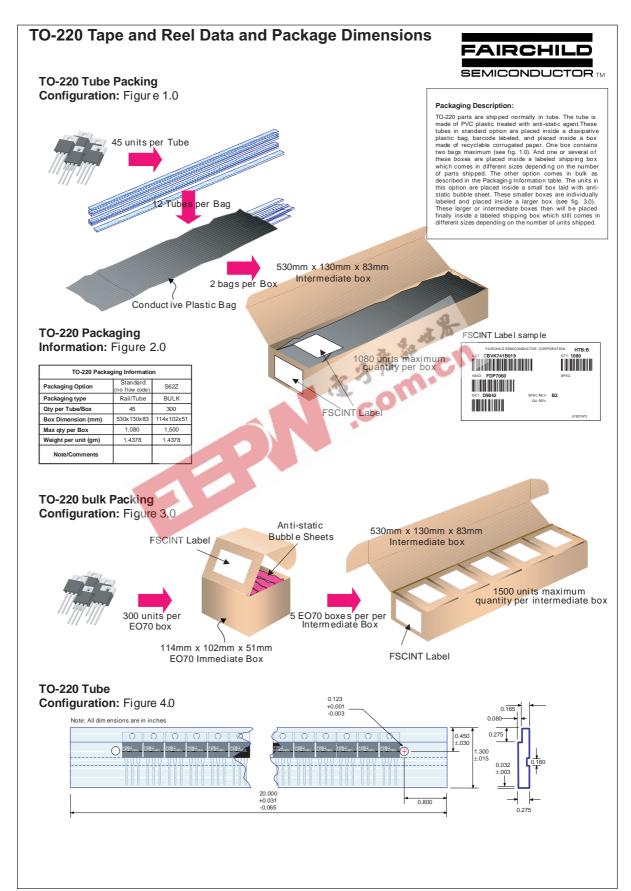
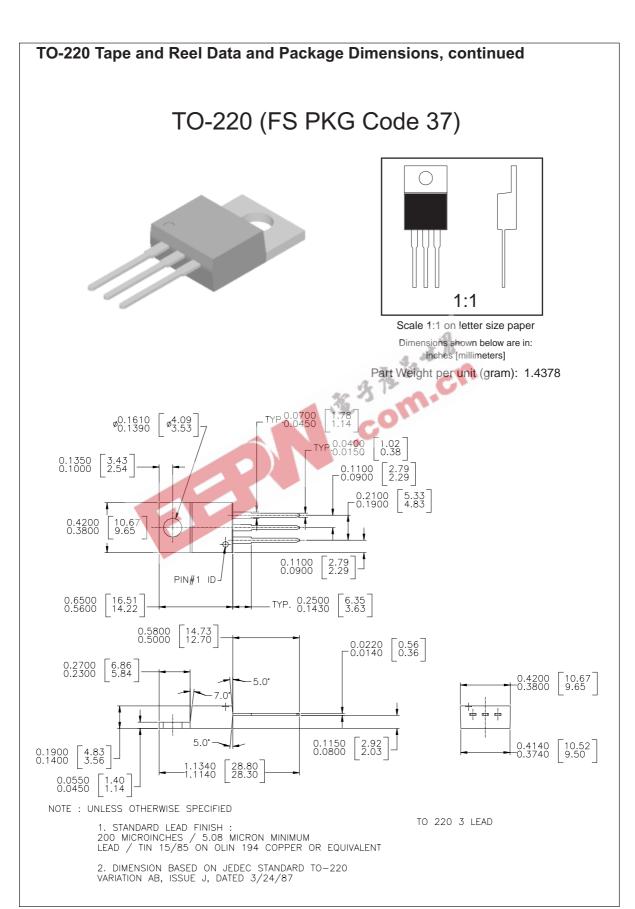
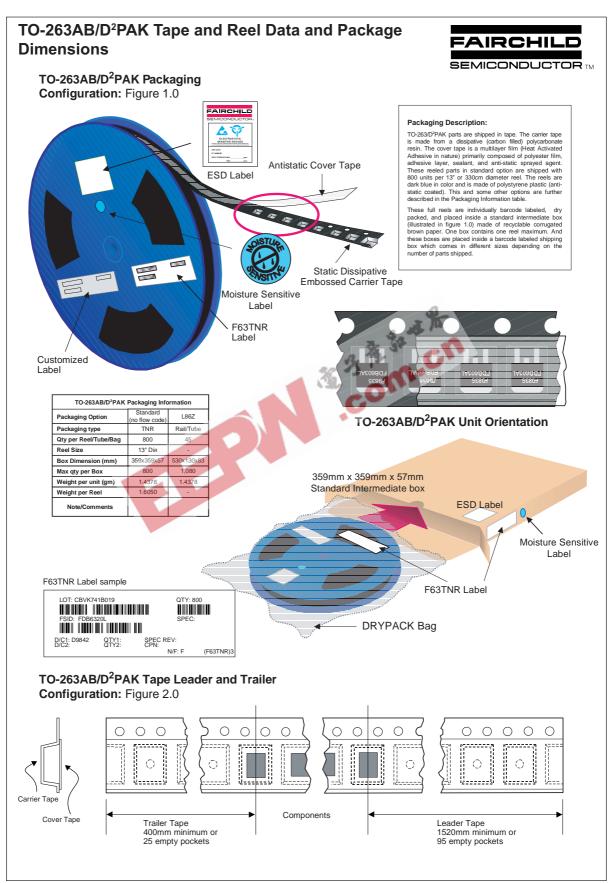


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

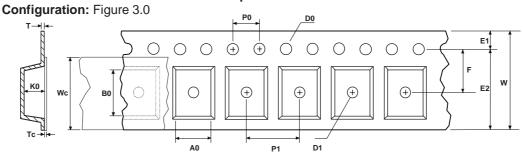






TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

TO-263AB/D²PAK Embossed Carrier Tape

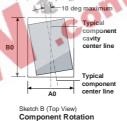




	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
TO263AB/ D²PAK (24mm)	10.60 +/-0.10	15.80 +/-0.10	24.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	22.25 min	11.50 +/-0.10	16.0 +/-0.1	4.0 +/-0.1	4.90 +/-0.10	0.450 +/-0.150	21.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).





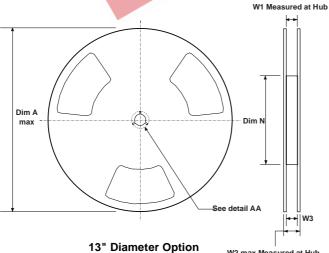


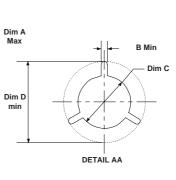
Sketch C (Top View)

Component lateral movement

TO-263AB/D²PAK Reel Configuration:

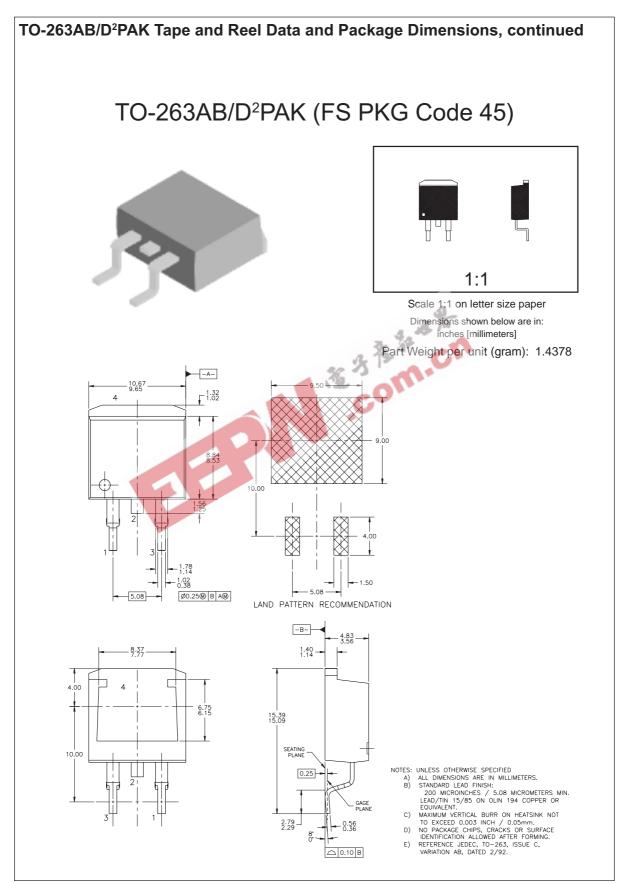
Figure 4.0





W2 max Measured at Hub

Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
24mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.961 +0.078/-0.000 24.4 +2/0	1.197 30.4	0.941 - 0.1.079 23.9 - 27.4



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